Thyristor Semiconductor Device - Page 1 of 2



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Inclosure Material:

Metal

Overall Length:

1.646 inches

Overall Diameter:

0.650 inches

End Application:

5895-01-269-3572 an/mpn-14k landing control central; an/spn-43b, 43c; forrestal class cv; nimitz class cvn; simulator an/mpq-t3

Mounting Facility Quantity:

1

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-48

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Threaded stud

Overall Width Across Flats:

Between 0.544 inches and 0.562 inches

Thread Size:

0.250 inches

Criticality Code Justification:

Feat

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

1200.0 nonrepetitive peak reverse voltage and 1000.0 repetitive peak reverse voltage and 1000.0 repetitive peak off-state voltage

Current Rating Per Characteristic:

2.00 milliamperes forward current, average of standard range and 2.00 milliamperes forward current, average nanoamperes

Power Rating Per Characteristic:

60.0 watts small-signal input power, common-collector not applicable

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius ambient air

Special Features:

Weapon system essential

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 threaded stud and 2 tab, solder lug

Shelf Life:

N/a

- Unit Of Measure:
- --

Thyristor Semiconductor Device - Page 2 of 2



Demilitarization:

No

Fiig:

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